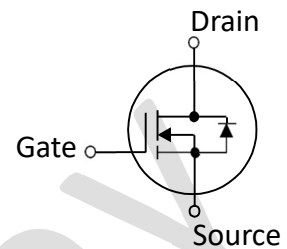


## 20V, 11A <sup>(1)</sup> N-Channel MOSFET

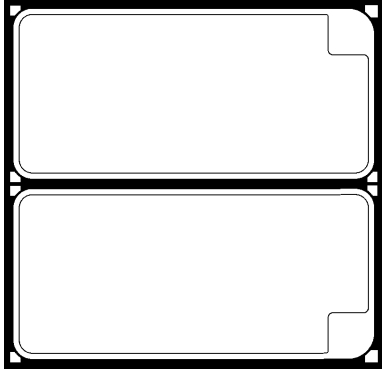
### SYMBOL

- Advanced Trench Device Design and Processes
- High Reliability Capability
- 100% CP Probing and Inking



### Electrical Characteristics in C/P Test (T<sub>J</sub> at 25 °C)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Condition
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	—	—	7.2	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 1A <sup>(2)</sup>
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	—	—	10.2	mΩ	V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 1A <sup>(2)</sup>
V <sub>GS(th)</sub>	Gate Threshold Voltage	0.5	—	1.5	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	1	μA	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V
I <sub>GSS</sub>	Gate-Body Leakage Current	—	—	±100	nA	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±12V
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature	-55°C to 150°C Max.				

Mechanical Data		Die Drawing
Chip Size	1462 μm X 1420 μm	
Gate Pad Size	180 μm X 180 μm	
Source Pad Size	1234 μm X 631 μm	
Scribe Line Width	60 μm	
Wafer Thickness	150 μm	
Wafer Diameter	200 mm	
Gross Die	12827 EA	
Source Metallization	Al-Cu (4μm typical)	
Drain Metallization	Ti-Ni-Ag	
Passivation	N/A	
Recommended Storage Environment	Store in original container, in dry nitrogen, 6 months at ambient temperature of 23°C ± 3°C	

(1) This characteristic assumes the die is assembled in SO-8 package. Actual performance may degrade when assembled.

(2) Pulse Width t<sub>p</sub> = < 300 μS, Duty Cycle < 2%.

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